

26. (Amended) The method of fabricating a thin film transistor according to claim 25, wherein the substrate includes [one of a glass and an oxide layer on a glass] a material selected from the group consisting of a glass and a glass having an oxide layer formed thereon.

27. (Amended) The method of fabricating a thin film transistor according to claim 25, wherein the substrate [is prepared by depositing a silicon wafer or an oxide layer on a silicon wafer] includes a material selected from the group consisting of a silicon wafer and a silicon wafer having an oxide layer formed thereon.

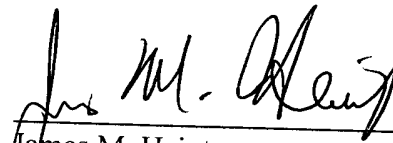
#### REMARKS

In view of the foregoing amendment, all claims are believed to be in condition for immediate allowance. Allowance of the application is respectfully solicited.

Respectfully submitted,

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